

CentralTM Semiconductor Corp.

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Manufacturers of World Class Discrete Semiconductors

2N5415

2N5416

Silicon PNP Transistor

JEDEC TO39 Case

DESCRIPTION

The CENTRAL SEMICONDUCTOR 2N5415 and 2N5416 are Silicon PNP Transistors designed for consumer and industrial line-operated applications.

MAXIMUM RATINGS ($T_A = 25^\circ\text{C}$)

		2N5415	2N5416	Unit
Collector-Base Voltage	VCBO	200	350	V
Collector-Emitter Voltage	VCEO	200	300	V
Emitter-Base Voltage	VEBO	4	6	V
Collector Current	IC	1.0	1.0	A
Base Current	IB	0.5	0.5	A
Power Dissipation	PT	1.0	1.0	W
Operating Temperature	TJ	-65 to 200		°C
Storage Temperature	Tstg	-65 to 200		°C

ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$)

Symbol	Test Conditions	Min	Max	Unit
2N5415				
ICBO	VCB = 175V		50	uA
ICEV	VCE = 200V, VEB = 1.5V		50	uA
ICEO	VCE = 150V		50	uA
IEBO	VEB = 4.0V		20	uA
VCEO	IC = 50mA	200		V
VCE(s)	IC = 50mA, IB = 5mA		2.5	V
VBE(s)	IC = 50mA, IB = 5mA		1.5	V
hFE	VCE = 10V, IC = 50mA	30	150	-
2N5416				
ICBO	VCB = 280V		50	uA
ICEV	VCE = 300V, VEB = 1.5V		50	uA
ICEO	VCE = 250V		50	uA
IEBO	VEB = 6.0V		20	uA
VCER	IC = 50mA, RBE = 50 ohms	350		V
VCEO	IC = 50mA	300		V
VCE(s)	IC = 50mA, IB = 5mA		2.0	V
VBE(s)	IC = 50mA, IB = 5mA		1.5	V
hFE	VCE = 10V, IC = 50mA	30	120	-